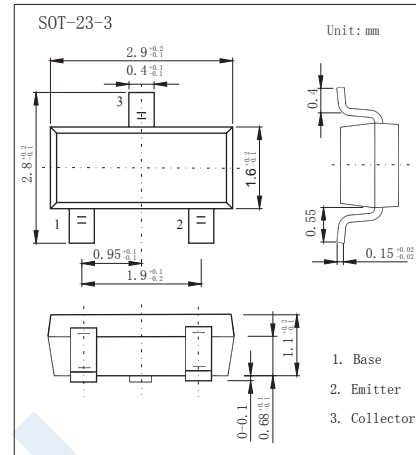


PNP Transistors

2SA1122-HF

■ Features

- Low frequency amplifier
- Pb-Free Package May be Available. The G-Suffix Denotes a Pb-Free Lead Finish



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-55	V
Collector to emitter voltage	V_{CEO}	-55	V
Emitter to base voltage	V_{EBO}	-5	V
Collector current	I_C	-100	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector to base breakdown voltage	$V_{(BR)CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-55			V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{ mA}, R_{BE} = \infty$	-55			V
Emitter to base breakdown voltage	$V_{(BR)EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-5			V
Collector cutoff current	I_{CBO}	$V_{CB} = -30\text{ V}, I_E = 0$			-0.1	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -4\text{ V}, I_C = 0$			-0.1	μA
DC current transfer ratio	h_{FE}	$V_{CE} = -12\text{ V}, I_C = -2\text{ mA}$	160		800	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10\text{ mA}, I_B = -1\text{ mA}$			-0.5	V
Base to emitter voltage	V_{BE}	$V_{CE} = -12\text{ V}, I_C = -2\text{ mA}$			-0.75	V

■ h_{FE} Classification

Type	2SA1122-C-HF	2SA1122-D-HF	2SA1122-E-HF
Range	160-320	250-500	400-800
Marking	CC _F	CD _F	CE _F

PNP Transistors

2SA1122-HF

■ Typical Characteristics

